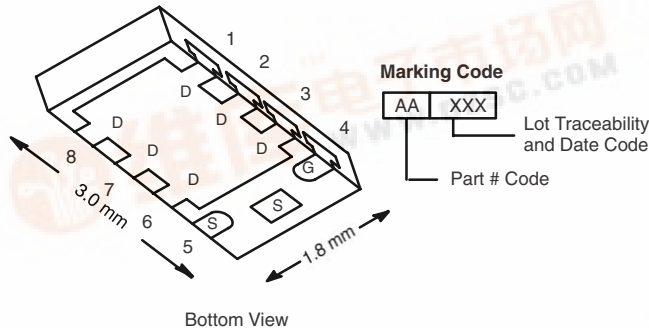


N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
60	0.034 at $V_{GS} = 10$ V	12	10.5 nC
	0.041 at $V_{GS} = 4.5$ V	12	

PowerPAK ChipFET Single



Bottom View

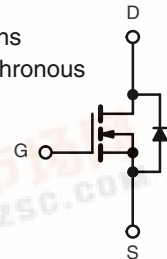
FEATURES

- Halogen-free
- TrenchFET[®] Power MOSFET
- New Thermally Enhanced PowerPAK[®] ChipFET[®] Package
 - Small Footprint Area
 - Low On-Resistance
 - Thin 0.8 mm Profile

RoHS
COMPLIANT

APPLICATIONS

- Load Switch for Portable Applications
- DC-DC Switch for Low Power Synchronous Rectification
- Intermediate Switch Driver for DC/DC Applications



Ordering Information: Si5476DU-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	$T_C = 25^\circ\text{C}$	12^a	A
	$T_C = 70^\circ\text{C}$	12^a	
	$T_A = 25^\circ\text{C}$	$7^{b,c}$	
	$T_A = 70^\circ\text{C}$	$5.6^{b,c}$	
Pulsed Drain Current	I_{DM}	25	A
Continuous Source-Drain Diode Current	$T_C = 25^\circ\text{C}$	12^a	
	$T_A = 25^\circ\text{C}$	$2.6^{b,c}$	
Avalanche Current	I_{AS}	15	mJ
Single Pulse Avalanche Energy	E_{AS}	11.2	
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	31	W
	$T_C = 70^\circ\text{C}$	20	
	$T_A = 25^\circ\text{C}$	$3.1^{b,c}$	
	$T_A = 70^\circ\text{C}$	$2^{b,c}$	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	$t \leq 5$ s	R_{thJA}	34	$^\circ\text{C/W}$
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	3	

Notes:

a. Package limited.

b. Surface Mounted on 1" x 1" FR4 board.

c. $t = 5$ s.d. See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under Steady State conditions is 90°C/W .

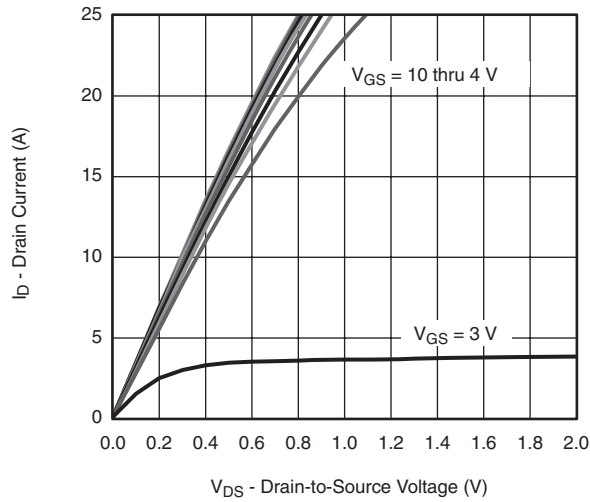
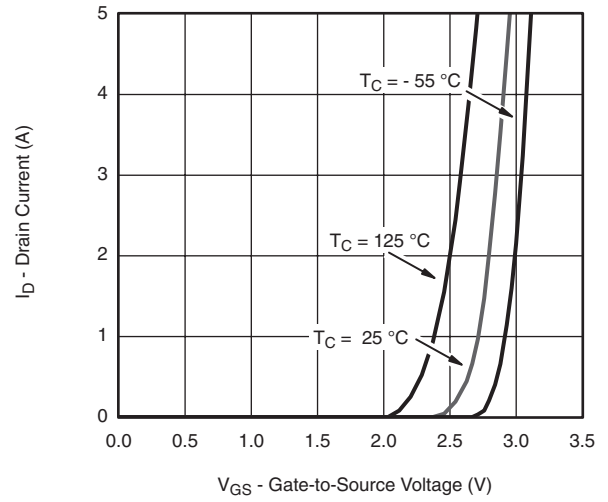
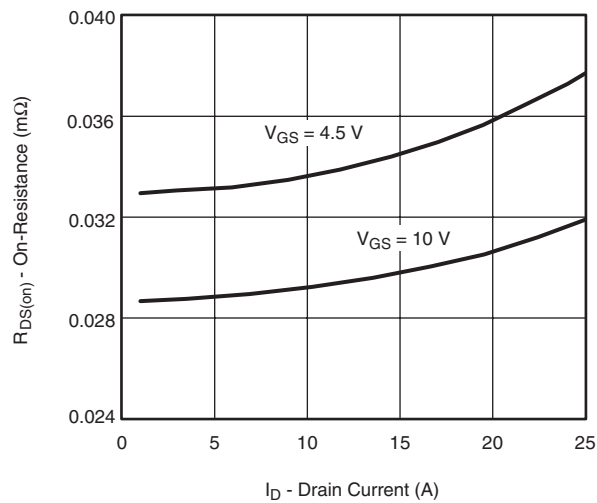
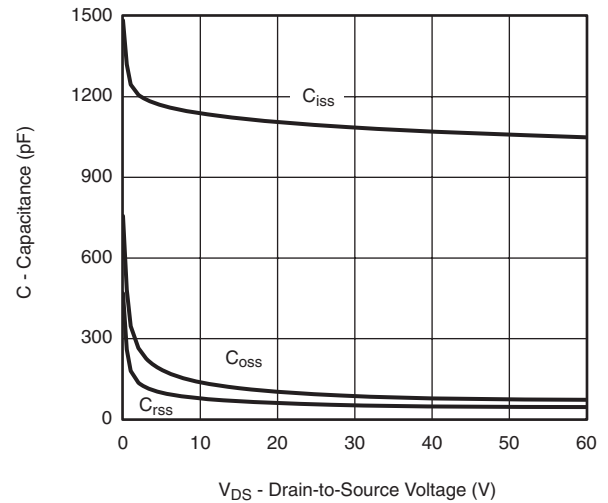
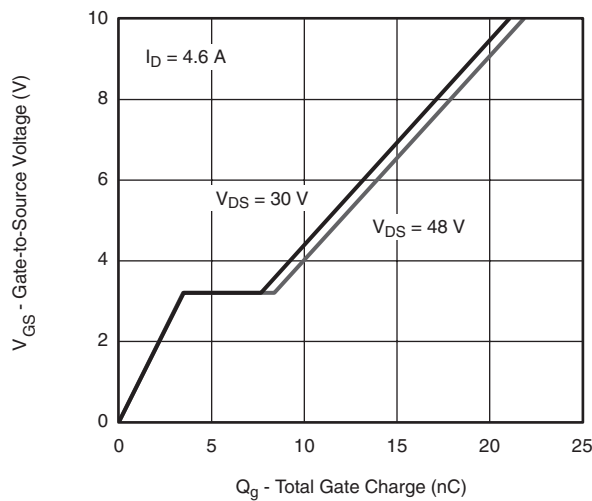
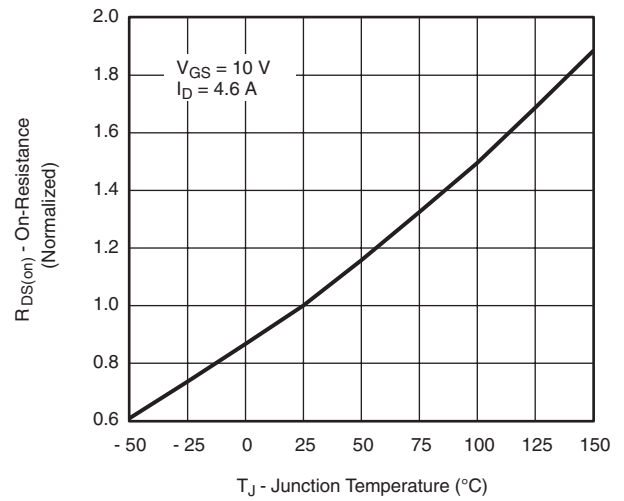
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 1 mA	60			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		55		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 6.3		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1		3	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			1	μA
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	25			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 4.6 A		0.028	0.034	Ω
		V _{GS} = 4.5 V, I _D = 4.2 A		0.033	0.041	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 4.6 A		20		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 30 V, V _{GS} = 0 V, f = 1 MHz		1100		pF
Output Capacitance	C _{oss}			90		
Reverse Transfer Capacitance	C _{rss}			55		
Total Gate Charge	Q _g	V _{DS} = 30 V, V _{GS} = 10 V, I _D = 4.6 A		21	32	nC
		V _{DS} = 30 V, V _{GS} = 4.5 V, I _D = 4.6 A		10.5	16	
Gate-Source Charge	Q _{gs}			3.5		
Gate-Drain Charge	Q _{gd}			4.2		
Gate Resistance	R _g	f = 1 MHz		3.3		Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 30 V, R _L = 5.4 Ω I _D ≅ 5.6 A, V _{GEN} = 4.5 V, R _g = 1 Ω		20	30	ns
Rise Time	t _r			150	225	
Turn-Off Delay Time	t _{d(off)}			20	30	
Fall Time	t _f			60	90	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 30 V, R _L = 5.4 Ω I _D ≅ 5.6 A, V _{GEN} = 10 V, R _g = 1 Ω		10	15	
Rise Time	t _r			15	25	
Turn-Off Delay Time	t _{d(off)}			22	40	
Fall Time	t _f			10	15	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			12	A
Pulse Diode Forward Current	I _{SM}				25	
Body Diode Voltage	V _{SD}	I _S = 5.5 A, V _{GS} = 0 V		0.85	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 5.5 A, dI/dt = 100 A/μs, T _J = 25 °C		25	50	ns
Body Diode Reverse Recovery Charge	Q _{rr}			25	50	nC
Reverse Recovery Fall Time	t _a			19		ns
Reverse Recovery Rise Time	t _b			6		

Notes:

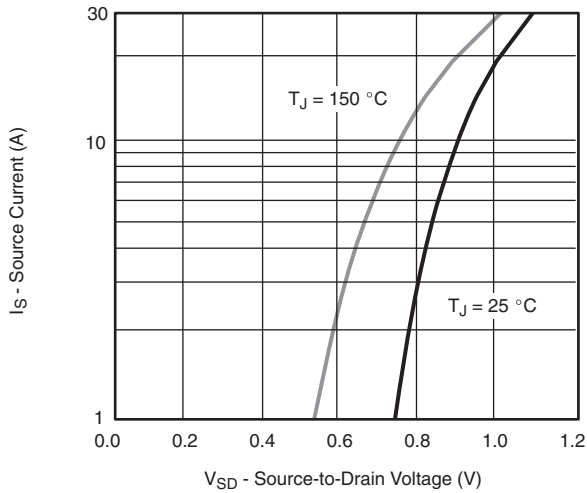
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

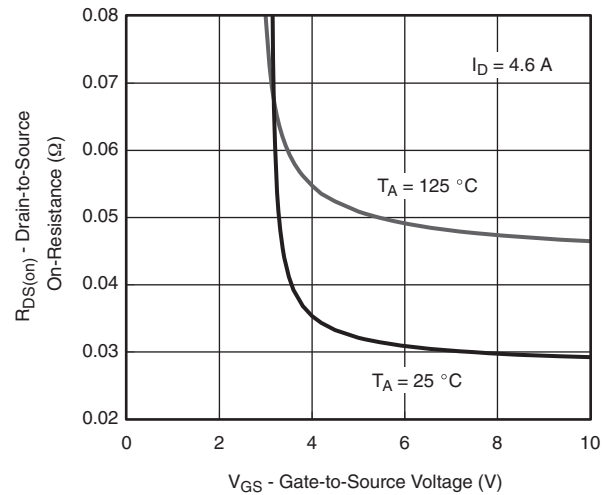
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current and Gate Voltage

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

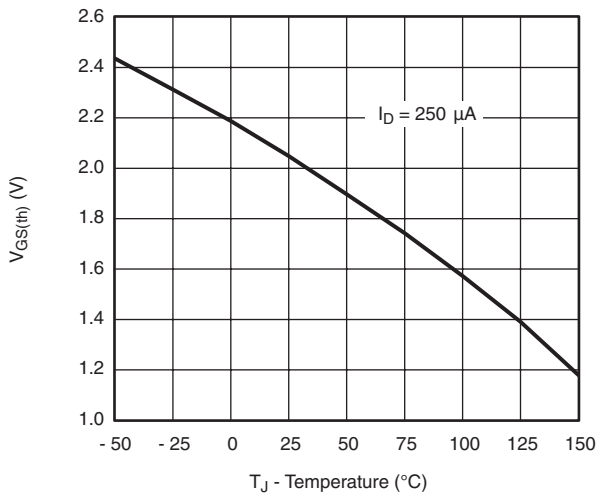
Si5476DU

[Vishay Siliconix 供应商](#)
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

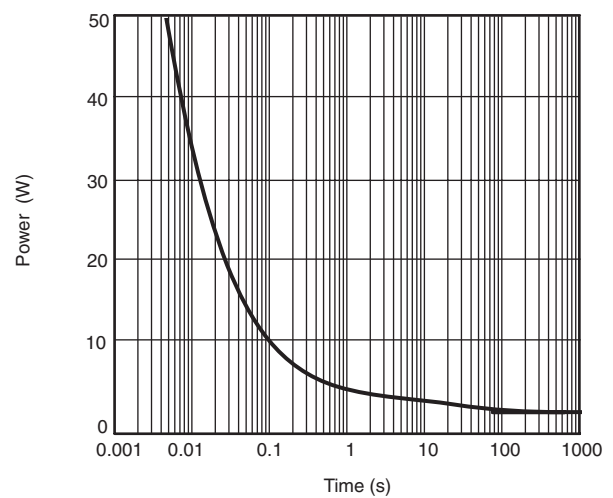
Source-Drain Diode Forward Voltage



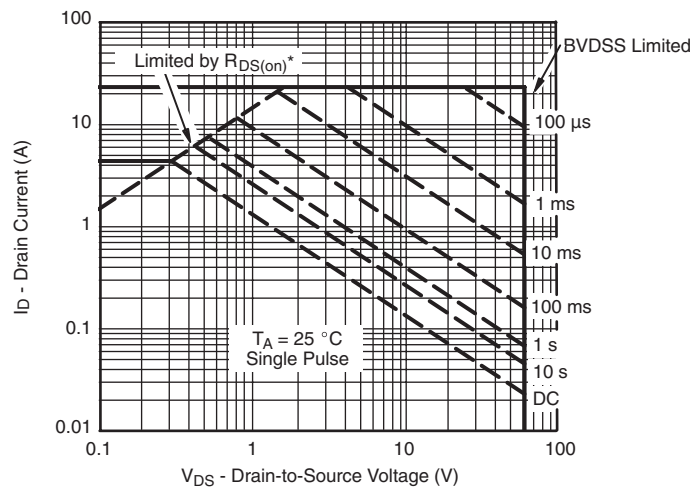
On-Resistance vs. Gate-to-Source Voltage



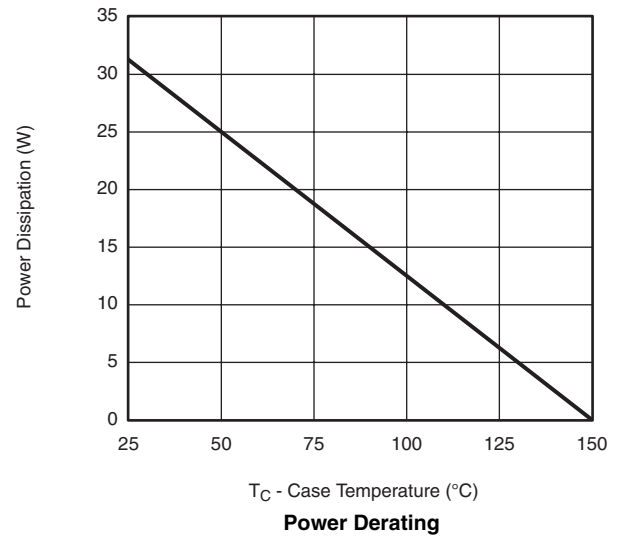
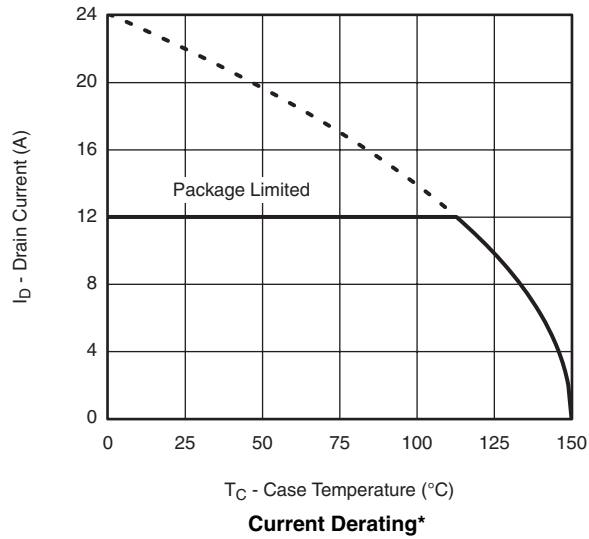
Threshold Voltage



Single Pulse Power, Junction-to-Ambient

* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

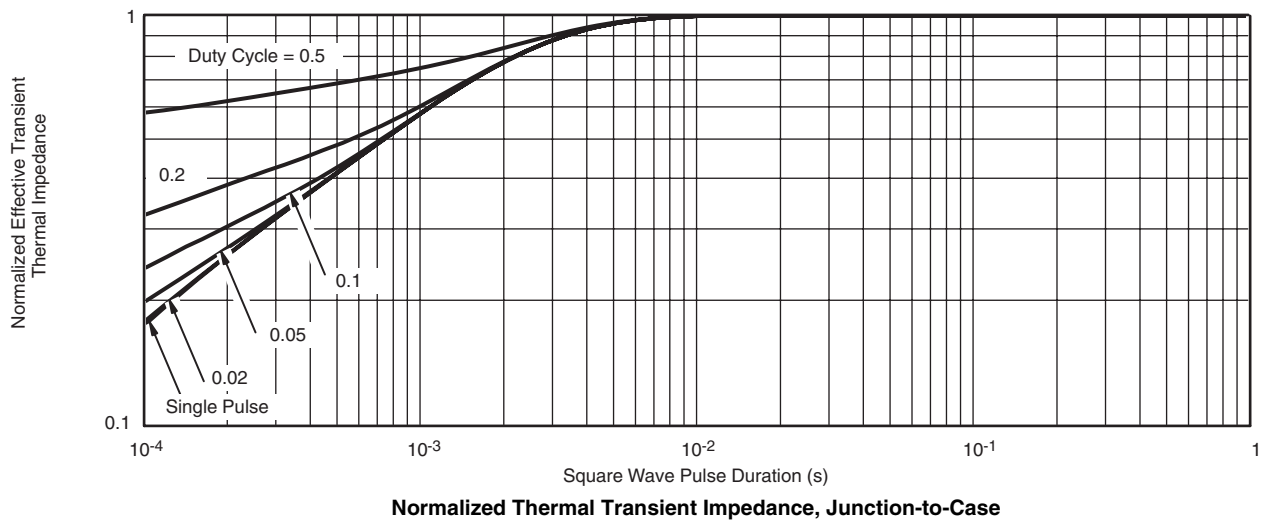
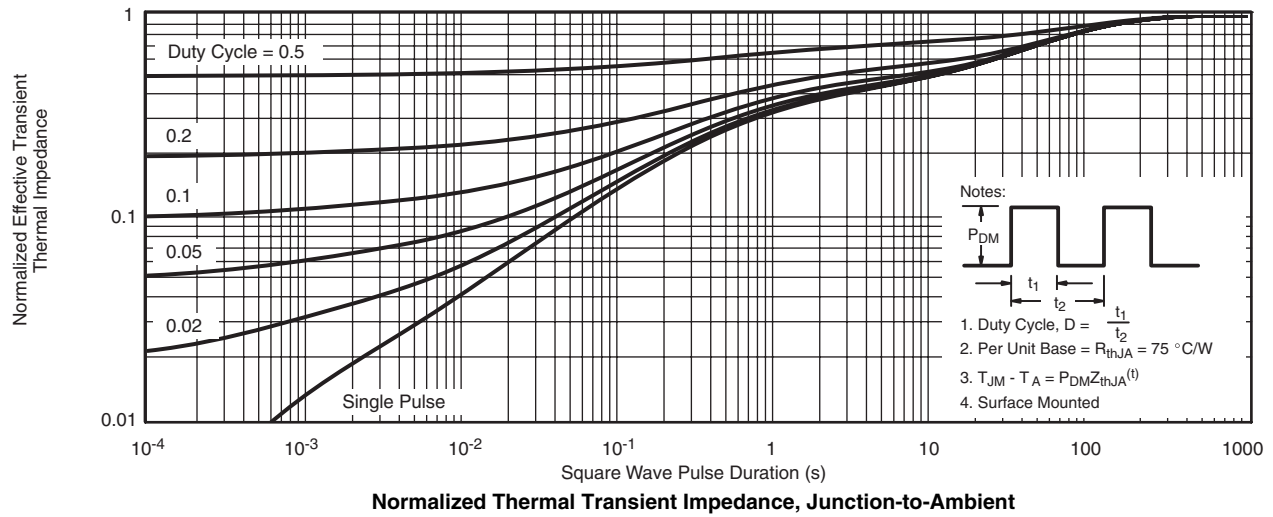
Safe Operating Area, Junction-to-Ambient


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

Si5476DU

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**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

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